

# **INCHANGE SEMICONDUCTOR**

# isc Silicon PNP Power Transistor

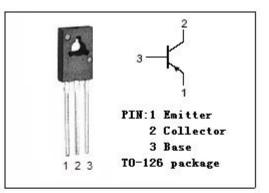
# 2SB986

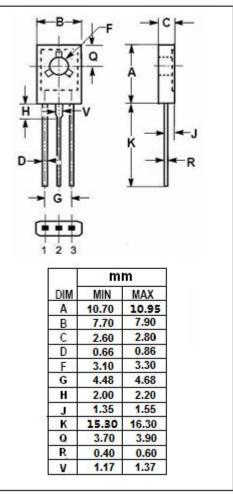
### DESCRIPTION

- High Collector Current-I<sub>C</sub>= -4.0A
- · Low Saturation Voltage -
  - : V<sub>CE(sat)</sub>= -0.5V(Max)@ I<sub>C</sub>= -2A, I<sub>B</sub>= -0.1A
- · Good Linearity of hFE
- Complement to Type 2SD1348
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

### APPLICATIONS

• Designed for power supplies, relay drivers, lamp drivers, electrical equipment applications.





#### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	-60	V	
VCEO	Collector-Emitter Voltage	-50	V	
V <sub>EBO</sub>	Emitter-Base Voltage	-6	V	
Ic	Collector Current-Continuous	-4	А	
ICP	Collector Current-Pulse	-6	A	
Pc	Collector Power Dissipation @ T <sub>a</sub> =25°C	1.2	— w	
	Collector Power Dissipation @ T <sub>C</sub> =25℃	10		
TJ	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C	

# <sup>1</sup> *isc & iscsemi* is registered trademark



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# ELECTRICAL CHARACTERISTICS

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = -10 μ A; I <sub>E</sub> = 0	-60			V
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>c</sub> = -1mA; R <sub>BE</sub> = ∞	-50			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage $I_E$ = -10 $\mu$ A; $I_C$ = 0		-6			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -2.0A; I <sub>B</sub> = -0.1A			-0.7	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -2.0A; I <sub>B</sub> = -0.1A			-1.2	V
I <sub>СВО</sub>	Collector Cutoff Current	V <sub>CB</sub> = -40V; I <sub>E</sub> = 0			-1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -4V; I <sub>C</sub> = 0			-1.0	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = -0.1A ; V <sub>CE</sub> = -2V	100		560	
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = -3A ; V <sub>CE</sub> = -2V	40			

### h<sub>FE-1</sub> Classifications

R	S	Т	U
100-200	140-280	200-400	280-560

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